

## Doping Furnace (Ultra Clean Samples)

- Forming **phosphorus diffusion**
- Gas phase diffusion
- Samples : Pieces – 4” wafer
- Phosphorous Doping
  - $\text{POCl}_3$  source
- Carrier gas:  $\text{N}_2$
- Drive-In Anneal
- Temperature: 780°C to 1050°C
- Trans-LC cleaning for tubes
  - Industry standard
  - Highly effective cleaning

